1 A very low V<sub>F</sub> MEGA Schottky barrier rectifiers Rev. 02 — 22 March 2007 Pro

Product data sheet

#### **Product profile** 1.

#### 1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifiers with an integrated guard ring for stress protection, encapsulated in small and flat lead Surface-Mounted Device (SMD) plastic packages.

#### Table 1. **Product overview**

Type number	Package	Package	
	NXP	JEITA	
PMEG3010CEH	SOD123F	-	single
PMEG3010CEJ	SOD323F	SC-90	single

#### 1.2 Features

- Forward current:  $I_F \le 1 A$
- Reverse voltage:  $V_R \le 30 \text{ V}$
- Very low forward voltage
- Small and flat lead SMD plastic packages

#### 1.3 Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Reverse polarity protection
- Low power consumption applications

#### 1.4 Quick reference data

#### Table 2. **Quick reference data**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>F</sub>	forward current	$T_{sp} \le 55 \ ^{\circ}C$	-	-	1	А
V <sub>R</sub>	reverse voltage		-	-	30	V
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 1 A	<u>[1]</u>	450	520	mV

[1] Pulse test:  $t_p \le 300 \ \mu s$ ;  $\delta \le 0.02$ .



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## 2. Pinning information

Pin	Description	Simplified outline Sy	ymbol
1	cathode	<u>[1]</u>	
2	anode	1 2	1 <u>-</u> 2 sym001
		001aab540	

[1] The marking bar indicates the cathode.

### 3. Ordering information

Table 4. Orderin	g information	l .	
Type number Package			
	Name	Description	Version
PMEG3010CEH	-	plastic surface-mounted package; 2 leads	SOD123F
PMEG3010CEJ	SC-90	plastic surface-mounted package; 2 leads	SOD323F

### 4. Marking

Table 5.	Marking codes	
Type nun	nber	Marking code
PMEG30 <sup>2</sup>	10CEH	C8
PMEG30 <sup>2</sup>	10CEJ	EN

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### 5. Limiting values

Table 6.Limiting valuesIn accordance with the Absolute Maximum Rating System (IEC 60134).						
Symbol	Parameter	Conditions	Min	Max	Unit	
V <sub>R</sub>	reverse voltage		-	30	V	
l <sub>F</sub>	forward current	$T_{sp} \le 55 \ ^{\circ}C$	-	1	А	
I <sub>FRM</sub>	repetitive peak forward current	$\begin{array}{l} t_p \leq 1 \text{ ms;} \\ \delta \leq 0.25 \end{array}$	-	7	А	
I <sub>FSM</sub>	non-repetitive peak forward current	square wave; t <sub>p</sub> = 8 ms				
	PMEG3010CEH		-	9	А	
	PMEG3010CEJ		-	10	А	
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$				
	PMEG3010CEH		<u>[1]</u> -	375	mW	
			[2] _	830	mW	
	PMEG3010CEJ		<u>[1]</u> -	350	mW	
			[2] _	830	mW	
Tj	junction temperature		-	150	°C	
T <sub>amb</sub>	ambient temperature		-65	+150	°C	
T <sub>stg</sub>	storage temperature		-65	+150	°C	

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.

### 6. Thermal characteristics

Table 7.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	<u>[1]</u>			
	PMEG3010CEH		[2] _	-	330	K/W
			[3] _	-	150	K/W
	PMEG3010CEJ		[2] _	-	350	K/W
			[3] _	-	150	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		<u>[4]</u>			
	PMEG3010CEH		-	-	60	K/W
	PMEG3010CEJ		-	-	55	K/W

 For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P<sub>R</sub> are a significant part of the total power losses.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.

[4] Soldering point of cathode tab.

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## 7. Characteristics

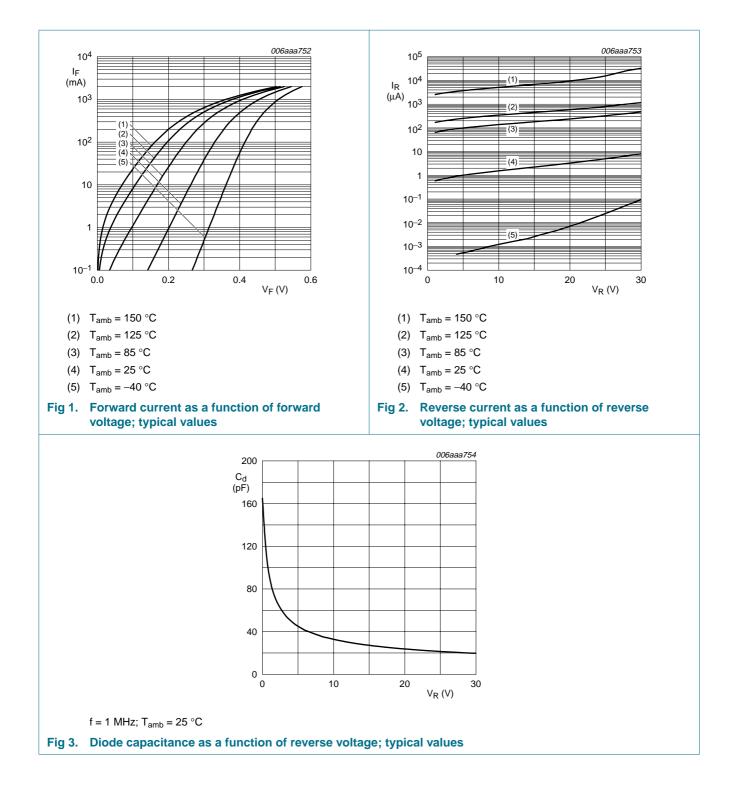
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>F</sub>	forward voltage		<u>[1]</u>			
		I <sub>F</sub> = 1 mA	-	200	240	mV
		I <sub>F</sub> = 10 mA	-	260	310	mV
		I <sub>F</sub> = 100 mA	-	330	390	mV
		I <sub>F</sub> = 500 mA	-	400	440	mV
		I <sub>F</sub> = 700 mA	-	420	450	mV
		I <sub>F</sub> = 1 A	-	450	520	mV
I <sub>R</sub>	reverse current	$V_R = 5 V$	-	1.2	-	μA
		V <sub>R</sub> = 10 V	-	1.8	-	μA
		V <sub>R</sub> = 30 V	-	10	50	μA
C <sub>d</sub>	diode capacitance	V <sub>R</sub> = 1 V; f = 1 MHz	-	90	100	pF

PMEG3010CEH\_PMEG3010CEJ\_2

#### **NXP Semiconductors**

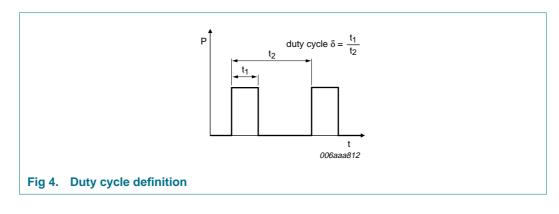
# PMEG3010CEH; PMEG3010CEJ

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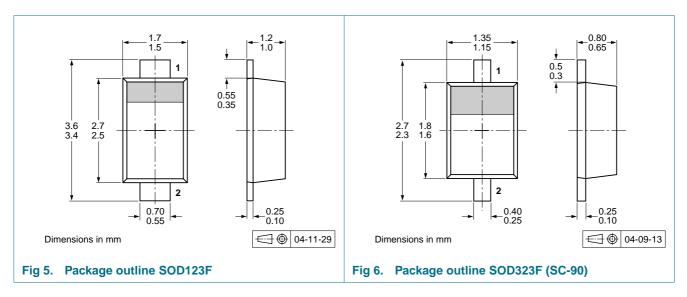


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### 8. Test information



### 9. Package outline



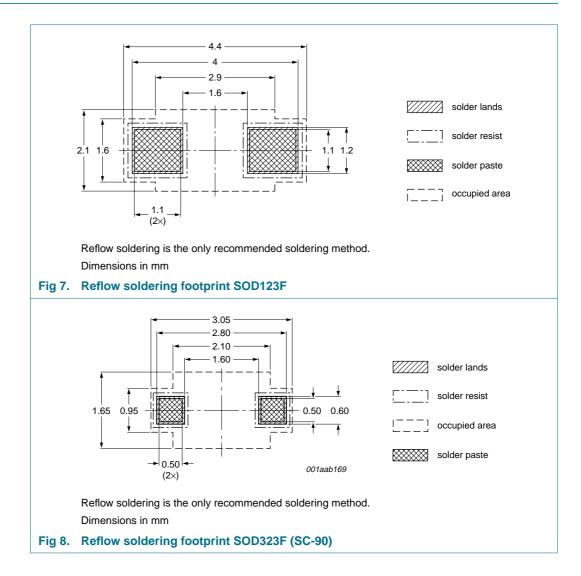
### **10. Packing information**

Table 9.Packing methodsThe indicated -xxx are the last three digits of the 12NC ordering code.[1]						
Type number	Package	Description	Packing qua	antity		
			3000	10000		
PMEG3010CEH	SOD123F	4 mm pitch, 8 mm tape and reel	-115	-135		
PMEG3010CEJ	SOD323F					

[1] For further information and the availability of packing methods, see <u>Section 14</u>.

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# 11. Soldering



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## 12. Revision history

#### Table 10.Revision history

-					
Document ID	Release date	Data sheet status	Change notice	Supersedes	
PMEG3010CEH_PMEG3010CEJ_2	20070322	Product data sheet	-	PMEG3010CEJ_1	
Modifications:		t of this data sheet has bee idelines of NXP Semicond	5	oly with the new	
	<ul> <li>Legal texts</li> </ul>	s have been adapted to the	new company name	where appropriate.	
	<ul> <li>Type number PMEG3010CEH added</li> </ul>				
	<ul> <li>Section 1.1 "General description": amended</li> </ul>				
	<ul> <li>Table 1 "Product overview": added</li> </ul>				
	Table 7 "The second	nermal characteristics": Tal	ole note 1 amended		
	• Table 8 "Characteristics": V <sub>F</sub> forward voltage maximum values amended				
	Section 8 '	'Test information": added			
PMEG3010CEJ_1	20060411	Product data sheet	-	-	

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### **13. Legal information**

#### 13.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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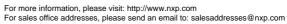
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